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BAT86

SMALL SIGNAL SCHOTTKY DIODES

Features

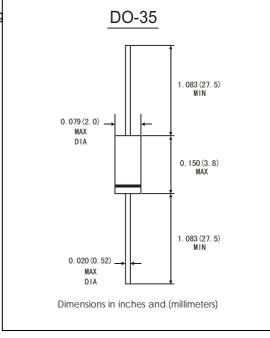
- For general purpose applications
- These diodes features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- These diode is also available in the Mini-MELF case with type designation LL86
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, and low logic applications.

MECHANICAL DATA

- Case: Do-35 glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13 gram

ABSOLUTE RATINGS (LIMITING VALUES)

	Symbols	Value	Units			
Repetitive Peak Reverse Voltage	V _R	50	V			
Forward Continuous Current at T =25°C	I _F	2001)	mA			
Repetitive Peak Forward Current at t<1s,ä< 0.5,T,=25°C	I _{FRM}	300 ¹⁾	mA			
Power Dissipation at T _A =65 ⁰ C	Ptot	2001)	mW			
Junction temperature	TJ	125	⁰ C			
Ambient Operating temperature Range	T _A	-55~+125	⁰ C			
Storage Temperature Range	T _{STG}	-55~+150	⁰ C			
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature						



ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Тур.	Мах.	Units
Reverse breakdown voltage Tested with 10 µA pulses	V(BR)R	50			٧
Forward voltage Pulse Test $t_p < 300 \mu s, \delta < 2\%$ at $I_F = 0.1 mA$, at $I_F = 1 mA$, at $I_F = 10 mA$, at $I_F = 10 mA$, at $I_F = 30 mA$, at $I_F = 100 mA$	VF VF VF VF		0.200 0.272 0.365 0.460 0.700	0.300 0.380 0.450 0.600 0.900	V V V V
Leakage current VR=25V	lR		0.2	0.5	μА
Junction Capacitance at VR=1V ,f=1MHz	C1			8	pF
Reverse recovery time Form I _F =10mA,I _R =10mA,I _R =1mA	trr			5	ns
Thermal resistance junction to ambient Air	Reja			300 1)	K/W
1) Valid provided that leads at a distance of 4mm from cas	se are kept at ambient to	emperature(DO-35)		